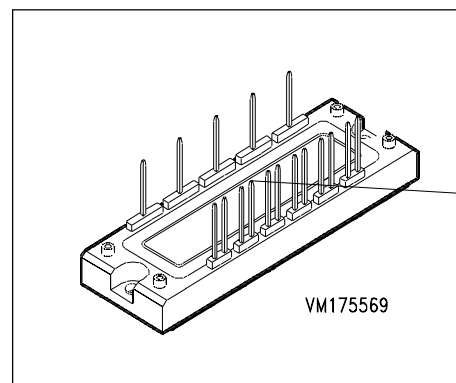


IGBT Power Module



		Values	Unit
Collector-emitter voltage	V_{CE}	1200	V
Collector-gate voltage $R_{GE} = 20 \text{ k}\Omega$	V_{CGR}	1200	
Gate-emitter voltage	V_{GE}	± 20	
DC collector current $T_C = 25 \text{ }^\circ\text{C}$ $T_C = 80 \text{ }^\circ\text{C}$	I_C	35 25	A
Pulsed collector current, $t_p = 1 \text{ ms}$ $T_C = 25 \text{ }^\circ\text{C}$ $T_C = 80 \text{ }^\circ\text{C}$	I_{Cpuls}	70 50	
Power dissipation per IGBT $T_C = 25 \text{ }^\circ\text{C}$	P_{tot}	200	W
Chip temperature	T_j	+ 150	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 ... + 125	
Thermal resistance, chip case	R_{thJC}	≤ 0.6	K/W
Diode thermal resistance, chip case	R_{thJCD}	≤ 1	
Insulation test voltage, $t = 1 \text{ min.}$	V_{is}	2500	Vac
Creepage distance	-	16	mm
Clearance	-	11	
DIN humidity category, DIN 40 040	-	F	sec
IEC climatic category, DIN IEC 68-1	-	40 / 125 / 56	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static Characteristics

Gate threshold voltage $V_{GE} = V_{CE}, I_C = 1\text{ mA}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter saturation voltage $V_{GE} = 15\text{ V}, I_C = 25\text{ A}, T_j = 25\text{ °C}$ $V_{GE} = 15\text{ V}, I_C = 25\text{ A}, T_j = 125\text{ °C}$	$V_{CE(sat)}$	-	2.5 3.1	3 3.7	
Zero gate voltage collector current $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 25\text{ °C}$ $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 125\text{ °C}$	I_{CES}	-	0.5 2	0.8 -	mA
Gate-emitter leakage current $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	-	-	180	nA

AC Characteristics

Transconductance $V_{CE} = 20\text{ V}, I_C = 25\text{ A}$	g_{fs}	10	-	-	S
Input capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{iss}	-	1650	-	pF
Output capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{oss}	-	250	-	
Reverse transfer capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{rss}	-	110	-	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

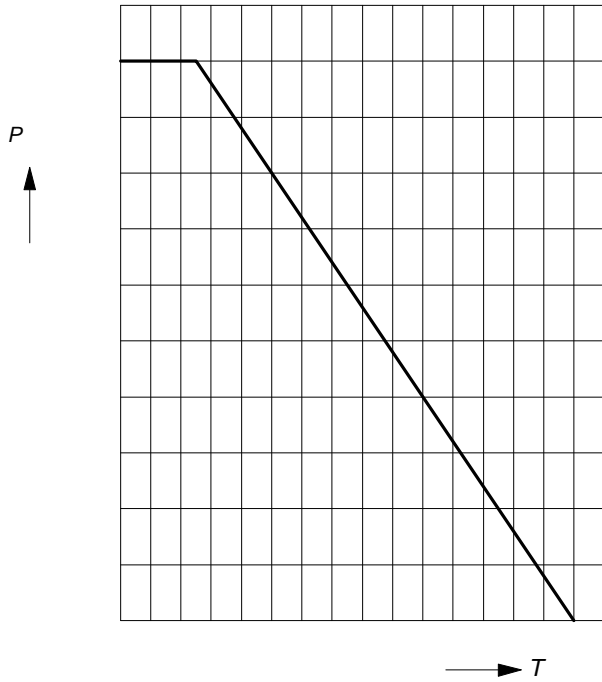
Switching Characteristics, Inductive Load at $T_j = 125\text{ °C}$

Turn-on delay time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 25\text{ A}$ $R_{Gon} = 47\ \Omega$	$t_{d(on)}$	-	75	150	ns
Rise time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 25\text{ A}$ $R_{Gon} = 47\ \Omega$	t_r	-	65	130	
Turn-off delay time $V_{CC} = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 25\text{ A}$ $R_{Goff} = 47\ \Omega$	$t_{d(off)}$	-	400	600	
Fall time $V_{CC} = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 25\text{ A}$ $R_{Goff} = 47\ \Omega$	t_f	-	50	100	

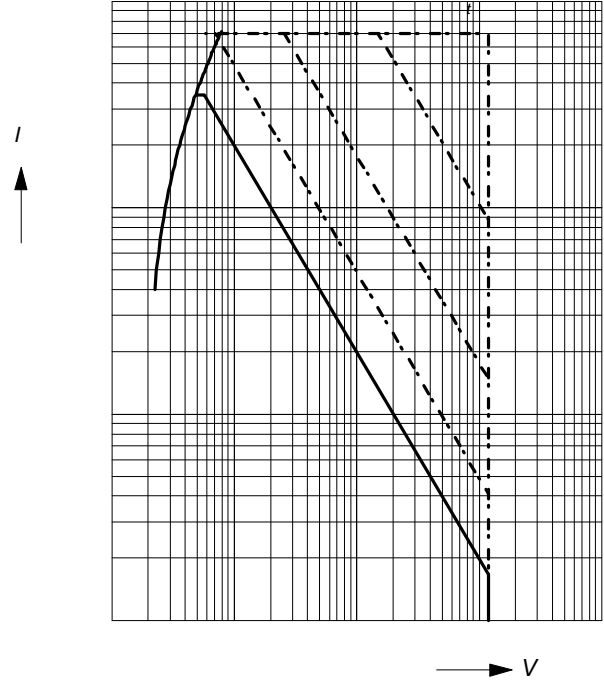
Free-Wheel Diode

Diode forward voltage $I_F = 25\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 25\text{ °C}$ $I_F = 25\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$	V_F	-	2.3	2.8	V
		-	1.8	-	
Reverse recovery time $I_F = 25\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -800\text{ A}/\mu\text{s}$, $T_j = 125\text{ °C}$	t_{rr}	-	0.13	-	μs
Reverse recovery charge $I_F = 25\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -800\text{ A}/\mu\text{s}$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	Q_{rr}	-	2.3	-	μC
		-	6	-	

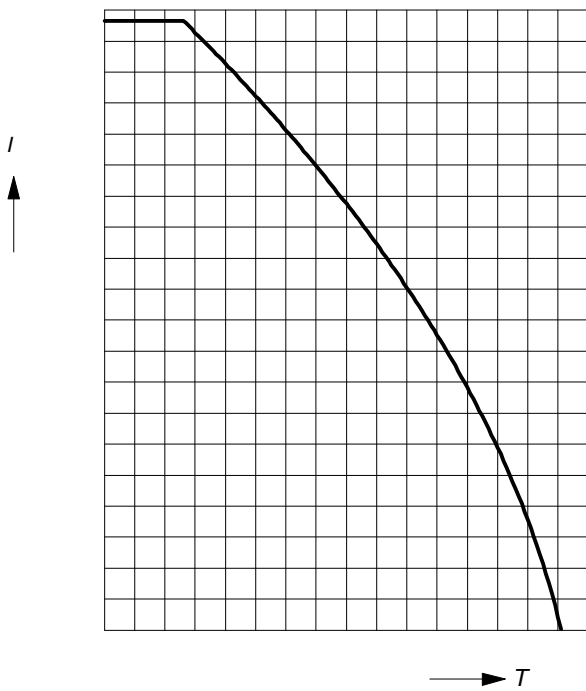
$P \quad f \quad T$
 $T \leq$



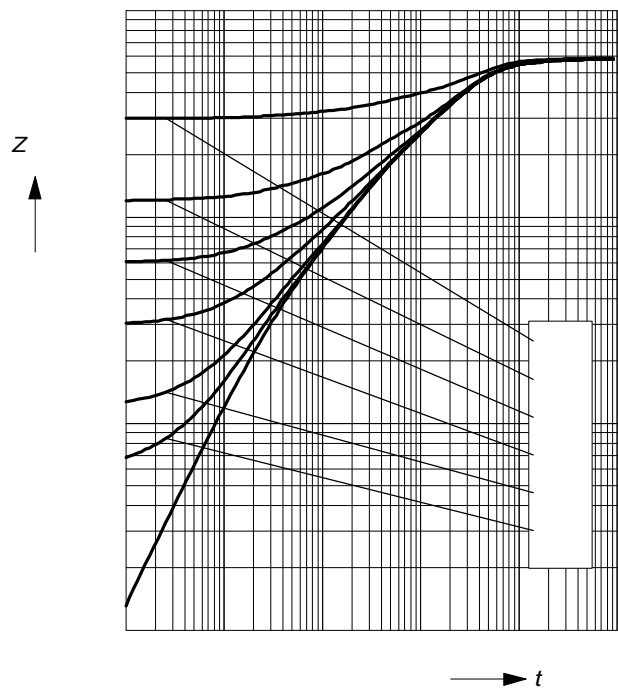
$I \quad f \quad V$
 $D, T \quad T \leq$



$I \quad f \quad T$
 $V \geq \quad T \leq$



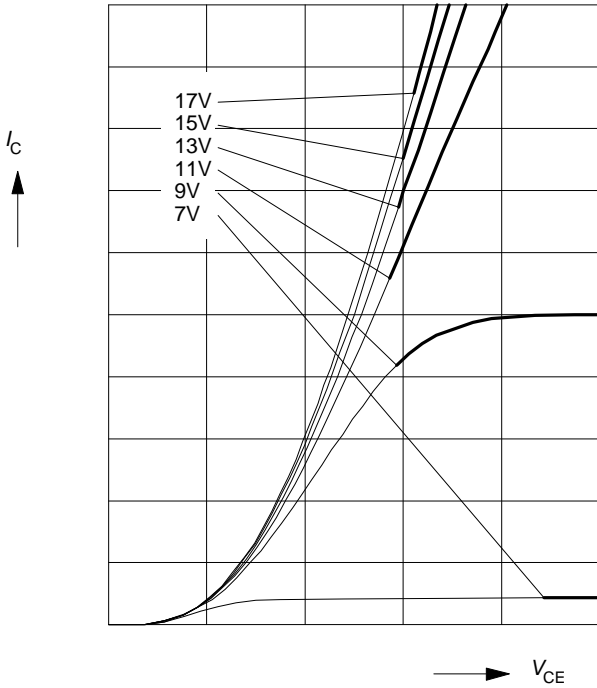
$Z \quad f \quad t$
 $D = t \quad T$



Typ. output characteristics

$I_C = f(V_{CE})$

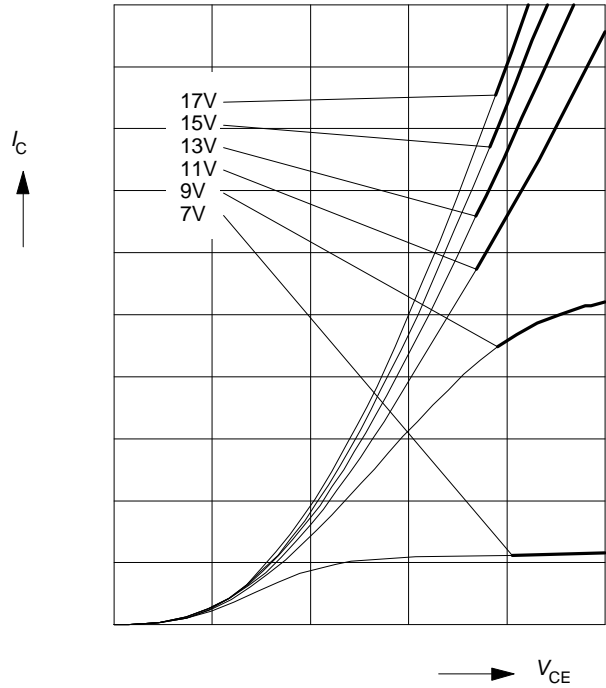
parameter: $t_p = 80 \mu s, T_j = 25 \text{ }^\circ\text{C}$



Typ. output characteristics

$I_C = f(V_{CE})$

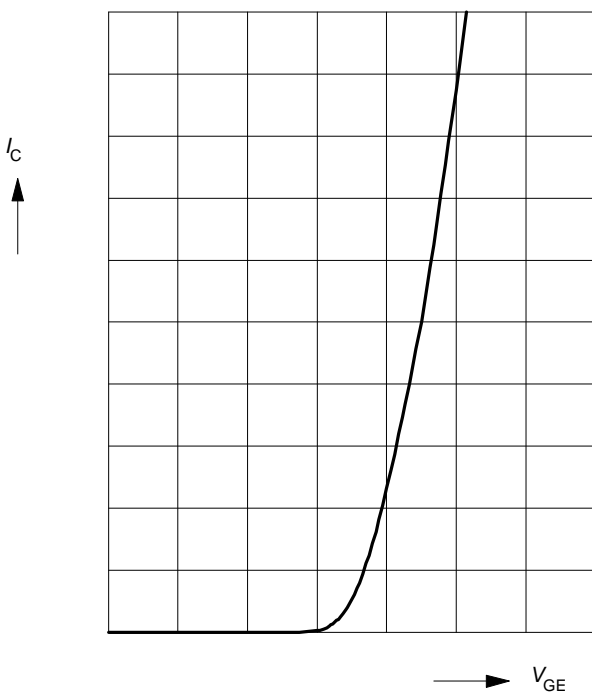
parameter: $t_p = 80 \mu s, T_j = 125 \text{ }^\circ\text{C}$



Typ. transfer characteristics

$I_C = f(V_{GE})$

parameter: $t_p = 80 \mu s, V_{CE} = 20 \text{ V}$

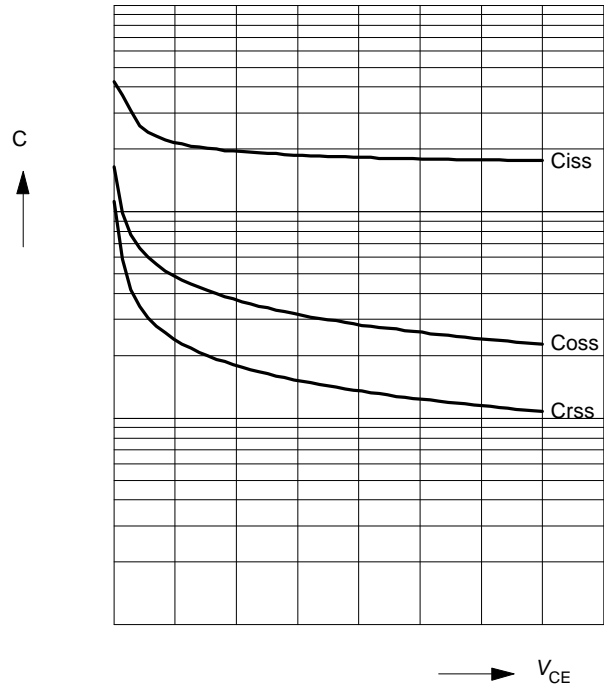
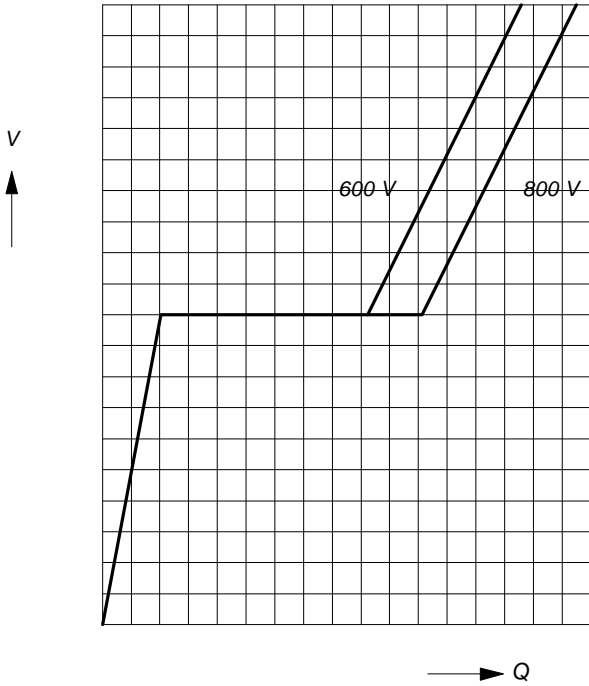


V f Q
 I

Typ. capacitances

$C = f(V_{CE})$

parameter: $V_{GE} = 0$ V, $f = 1$ MHz



Reverse biased safe operating area

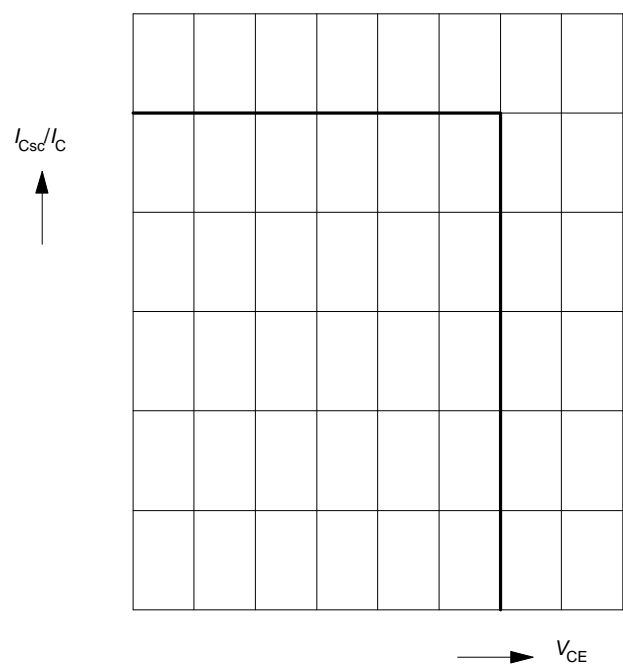
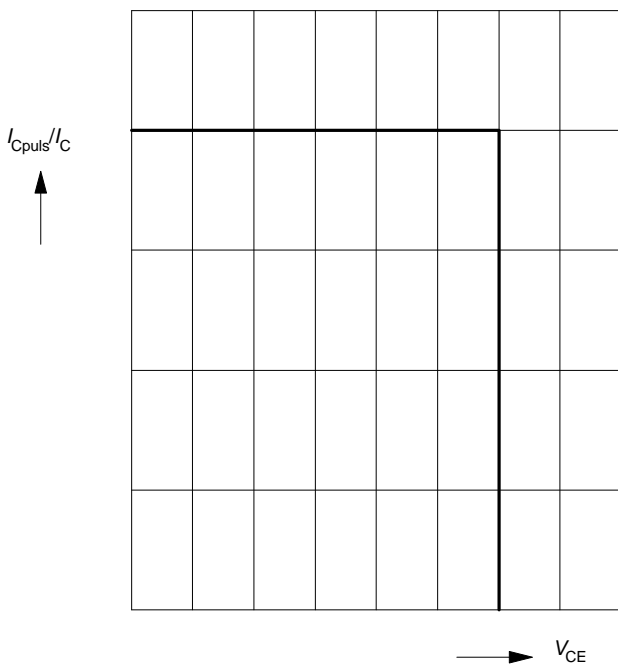
$I_{Cpuls} = f(V_{CE})$, $T_j = 150^\circ\text{C}$

parameter: $V_{GE} = 15$ V

Short circuit safe operating area

$I_{Csc} = f(V_{CE})$, $T_j = 150^\circ\text{C}$

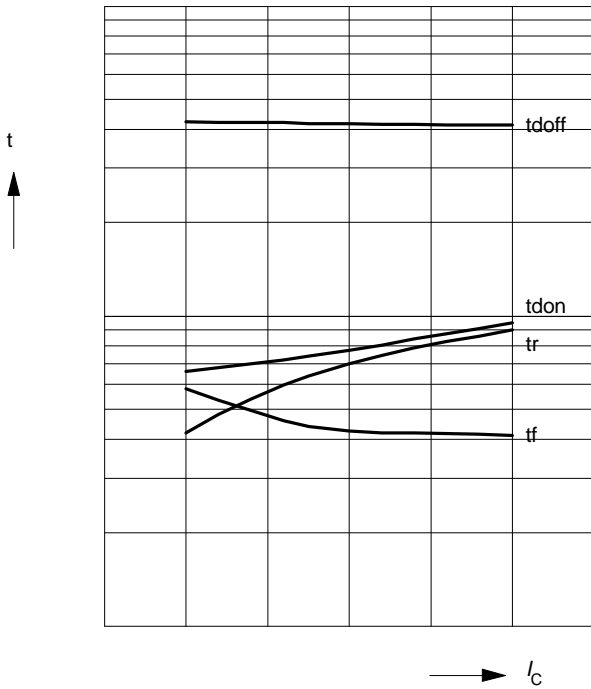
parameter: $V_{GE} = \pm 15$ V, $t_{SC} \leq 10$ μs , $L < 50$ nH



Typ. switching time

$t = f(I)$

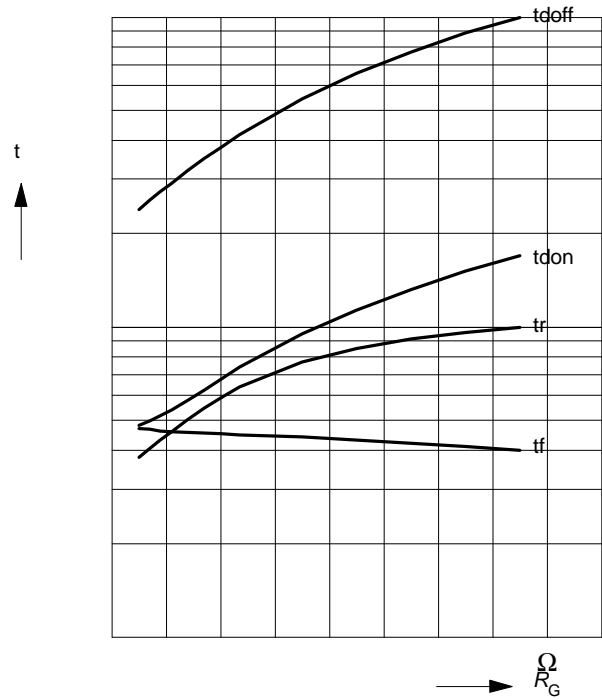
Ω



Typ. switching time

$t = f(R_G)$, inductive load, T_j = 125°C

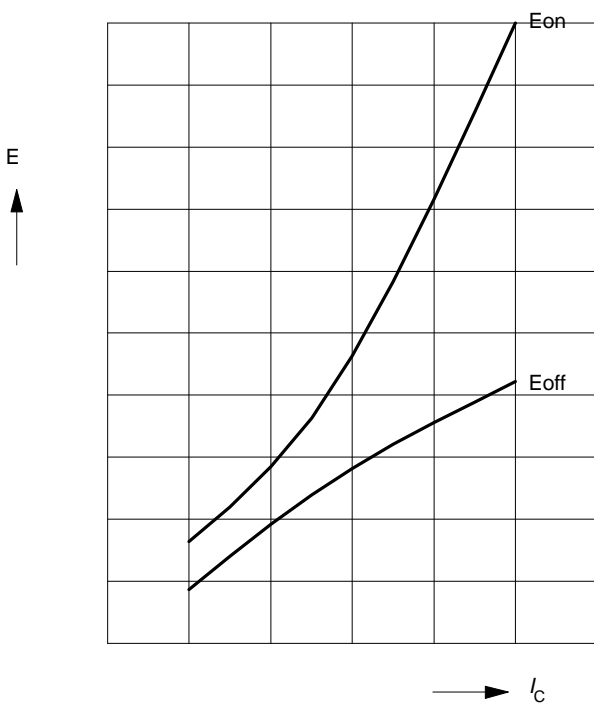
par.: V_{CE} = 600 V, V_{GE} = ± 15 V, I_C = 25 A



Typ. switching losses

$E = f(I_C)$, inductive load, T_j = 125°C

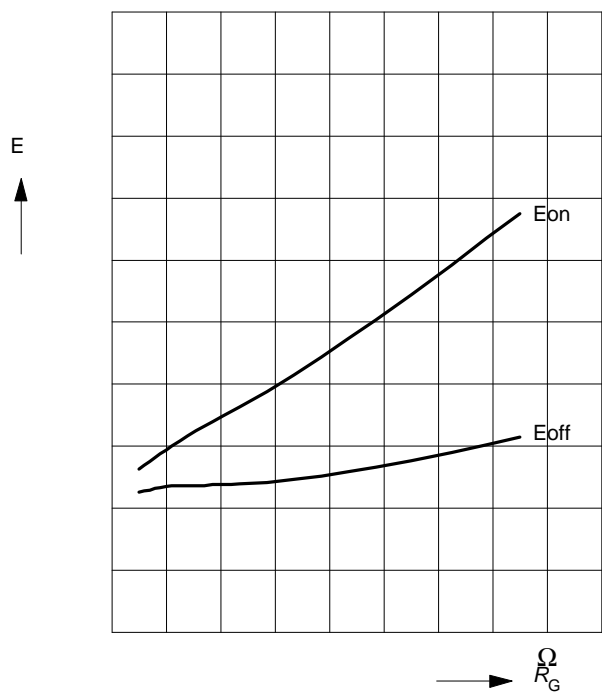
par.: V_{CE} = 600 V, V_{GE} = ± 15 V, R_G = 47 Ω



Typ. switching losses

$E = f(R_G)$, inductive load, T_j = 125°C

par.: V_{CE} = 600V, V_{GE} = ± 15 V, I_C = 25 A

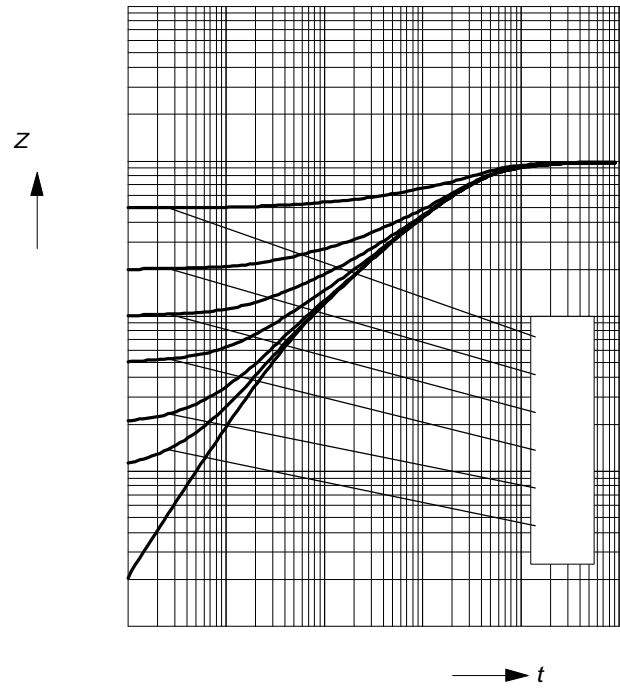
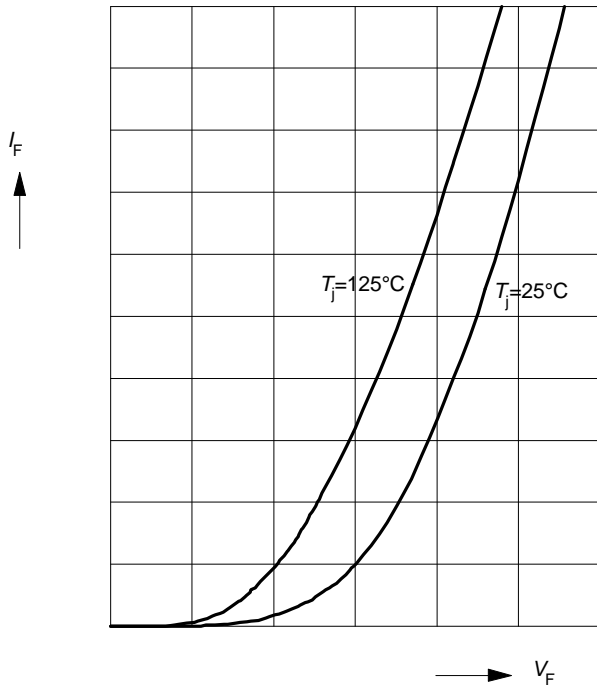


Forward characteristics of fast recovery

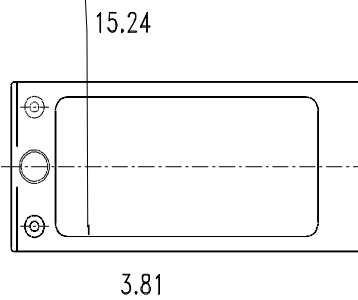
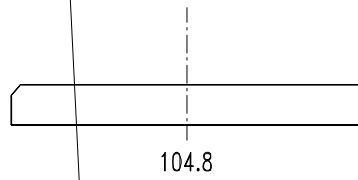
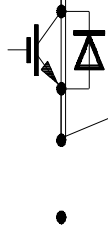
reverse diode $I_F = f(V_F)$

parameter: T_j

Z $f t$
 $D = t T$



Circuit Diagram Weight: 180 g



93
max.

GM175569

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